

**IN THE SPECIFICATION**

Please amend the first paragraph on page 15 of the specification as follows:

Next, an interlayer insulating film 13 is formed, a source electrode 17 and a drain electrode 18 are formed, a transparent electrode 20 is formed, and an alignment layer 21 is formed on the transparent electrode 20 in a manner similar to that in the conventional method. That is, in order to form the interlayer insulating film 13, a silicon nitride film 14 (50 to 500 nm) and a silicon oxide film 15 (50 to 500 nm) are continuously deposited, as shown in FIG. 3A. Next, contact holes 16 are made by etching the interlayer insulating film 13 and the gate protective insulating film ~~[[6]]~~ 8, as shown in FIG. 3B, and a metal, such as Al, is embedded in the contact holes 16 to form the source electrode 17 and the drain electrode 18, as shown in FIG. 3C. The planarizing layer 19 formed of an organic planarizing film composed of an organic acrylic resin, a silicon nitride planarizing film, or the like is formed in the region excluding a section for forming a contact with the transparent electrode of the liquid crystal display panel and a pad-forming section. The transparent electrode 20 composed of ITO or the like is then formed so as to cover the pixel section, and the alignment layer 21 is formed on the transparent electrode 20. Thus, a TFT substrate 201A for a liquid crystal display device having the TFT 100A of the present invention as the active element is obtained, as shown in FIG. 3D.